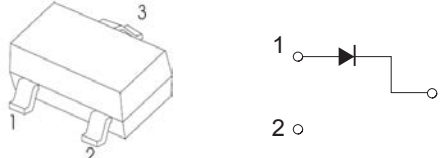


SWITCHING DIODE	SOT-23 Plastic-Encapsulate Diodes
<p>SOT-23</p>  <p>Marking :KA2</p>	<p>Features</p> <ul style="list-style-type: none"> • Fast Switching Speed • For General Purpose Switching Applications • High Conductance

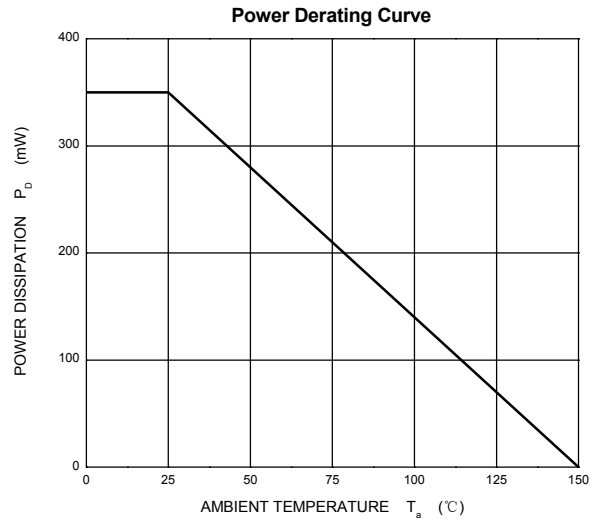
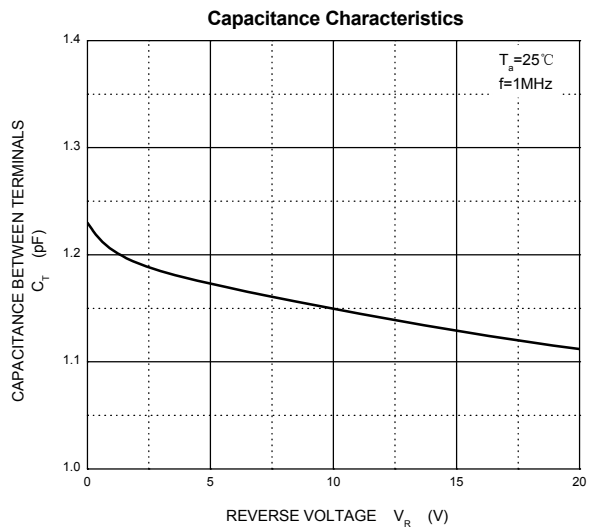
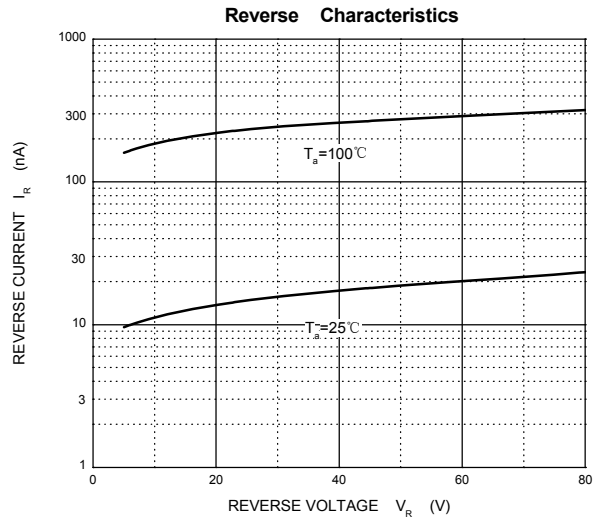
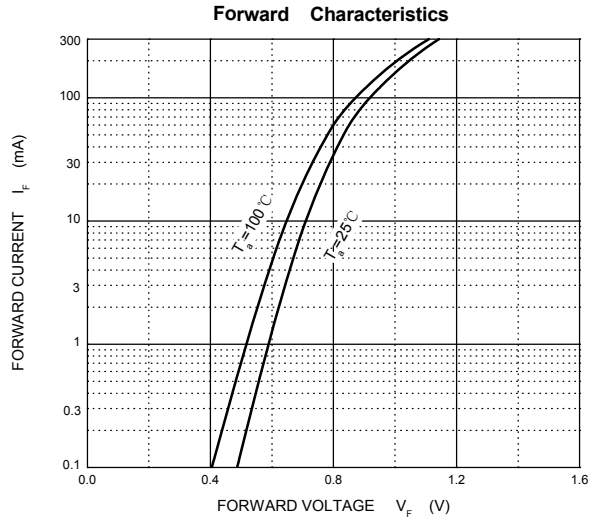
Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	75	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_o	150	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_d	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)}$	75			V	$I_R=100\mu A$
Forward voltage	V_{F1}			0.715	V	$I_F=1mA$
	V_{F2}			0.855	V	$I_F=10mA$
	V_{F3}			1.0	V	$I_F=50mA$
	V_{F4}			1.25	V	$I_F=150mA$
Reverse current	I_{R1}			2.5	μA	$V_R=75V$
	I_{R2}			25	nA	$V_R=20V$
Capacitance between terminals	C_T			2	pF	$V_R=0V, f=1MHz$
Reverse recovery time	t_{rr}			4	ns	$I_F=I_R=10mA$ $I_{rr}=0.1I_R, R_L=100\Omega$

Typical Characteristics



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)